

Silicon PNP Epitaxial Type Transistor

Features

High voltage and high current: VCEO = -50 V, IC = 150 mA (max)

• Low noise: NF = 1dB (typ.), 10dB (max)

· Small package

· RoHS compliant package

Mechanical Data

· Case: Molded plastic

• Epoxy: UL94-V0 rate flame retardant

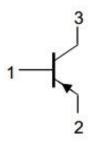
Packing & Order Information

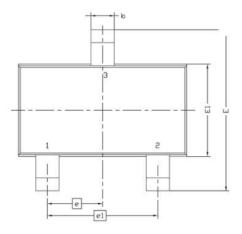
3,000/Reel

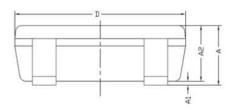


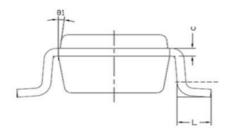
RoHS COMPLIANT

Graphic symbol









Cumbal	MILLIMETERS		
Symbol	MIN	MAX	
Α	0.8	1.2	
A1	0	0.1	
A2	0.7	1.1	
b	0.3	0.5	
С	0.1	0.2	
D	2.7	3.1	
E	2.6	3	
E1	1.4	1.8	
е	0.95 BSC		
e1	1.9 BSC		
L	0.3	0.6	
θ1	7° NOM		



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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

ABSOLUTE MAXIMUM RATING @ Ta=25°C unless otherwise specified					
Symbol	Parameter	Value	Unit		
V_{CBO}	Collector-Base Voltage	-50	V		
V_{CEO}	Collector-Emitter Voltage	-50	V		
V _{EBO}	Emitter-Base Voltage	-5	V		
I _C	Collector Current	-150	mA		
I _B	Base Current	-30	mA		
Pc	Collector Dissipation	150	mW		
Tj	Junction Temperature	125	°C		
Tstg	Storage Temperature Range	-55 to +125	°C		

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified						
Symbol	Parameter	Test Conditions	MIN	TYP	MAX	UNIT
I_{CBO}	Collector cut-off current	$V_{CB} = -50 \text{ V}$, $I_E = 0$			-0.1	μA
I _{EBO}	Emitter cut-off current	$V_{EB} = -5 \text{ V}$, $I_C = 0$			-0.1	μA
h _{FE}	DC current gain	$V_{CE} = -6 \text{ V}$, $I_{C} = -2 \text{ mA}$	70		400	
V _{CE(sat)}	Collector-emitter saturation voltage	$I_C = -100 \text{mA}$, $I_B = -10 \text{mA}$		-0.1	-0.3	V
f _T	Transition frequency	$V_{CE} = -10 \text{ V}$, $I_{C} = -1 \text{ mA}$		60		MHz
C _{ob}	Collector output capacitance	$V_{CB} = -10 \text{ V}, I_{E} = 0$ f = 1.0MHz		4	7	pF
NF	Noise figure	$V_{CE} = -6 \text{ V}, I_{C} = -0.1 \text{ mA}$ $f = 1.0 \text{KHz}, Rg = 10 \text{k}\Omega$		1.0	10	dB

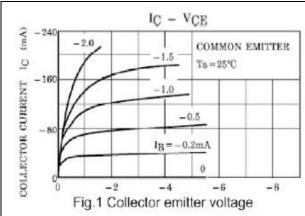
^{*}Pulse test: tp≤300μs, δ≤0.02.

h _{FE} CLASSIFICATION						
Marking	SO	SY	SR			
Rank	0	Y	GR			
Range	70-140	120~240	200-400			



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■Typical Characterisitics



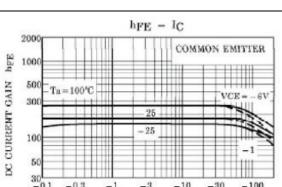
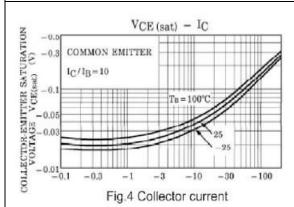
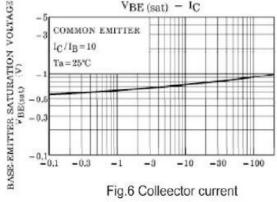
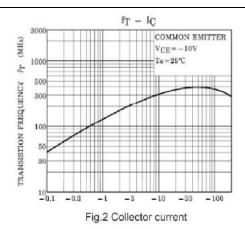


Fig.3 Collector current



VBE (sat) - IC





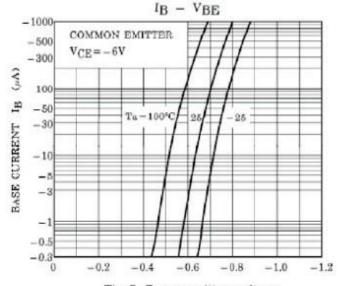


Fig.5 Base emitter voltage

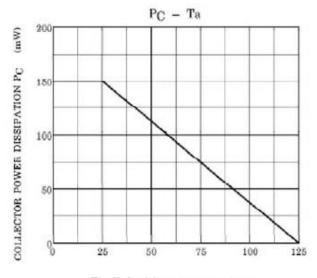


Fig.7 Ambient temperature



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